

MAPRST1214-30UF



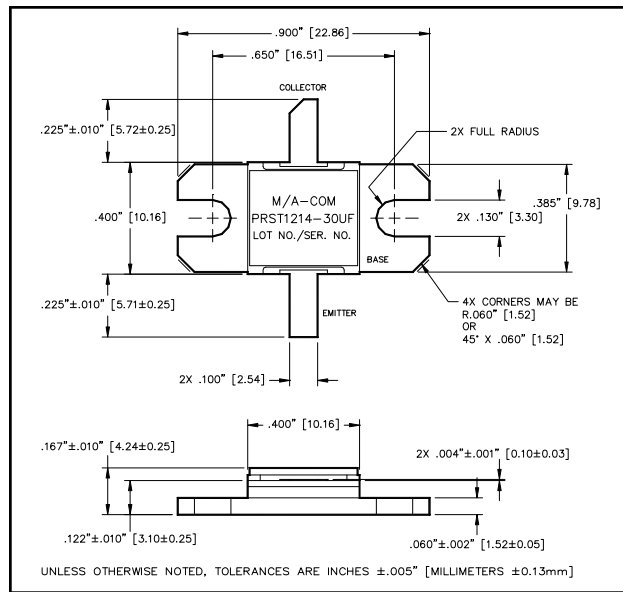
Radar Pulsed Power Transistor
30W, 1.2-1.4 GHz, 6ms Pulse, 25% Duty

M/A-COM Products
Released, 30 May 07

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	70	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	5.0	A
Power Dissipation @ +25°C	P_{TOT}	145	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$		BV_{CES}	70	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		I_{CES}	-	2.0	mA
Thermal Resistance	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	1.2	°C/W
Output Power	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	P_{OUT}	30	-	W
Power Gain	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	G_P	7.5	-	dB
Gain Flatness	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	ΔG	-	1.25	dB
Collector Efficiency	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	η_C	45	-	%
Input Return Loss	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-9	dB
Pulse Droop	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	Droop	-	0.5	dB
Load Mismatch Tolerance	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 36\text{V}$, $P_{in} = 5.3\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

MAPRST1214-30UF



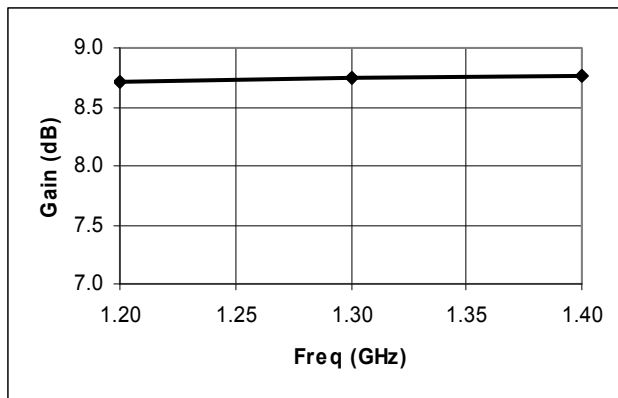
Radar Pulsed Power Transistor
30W, 1.2-1.4 GHz, 6ms Pulse, 25% Duty

M/A-COM Products
Released, 30 May 07

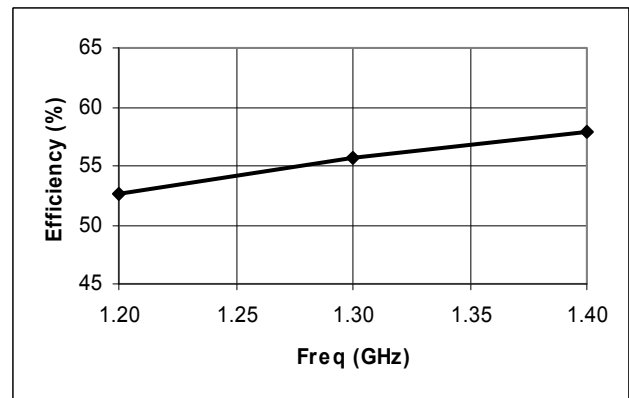
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	Droop (dB)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	5.3	39.4	8.71	2.08	52.6	0.24	-12.3	S	P
1.3	5.3	39.7	8.75	1.98	55.6	0.20	-14.6	S	P
1.4	5.3	39.9	8.77	1.92	57.8	0.17	-15.0	S	P

Gain vs. Frequency

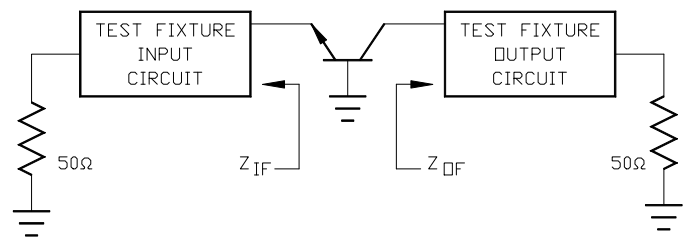


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

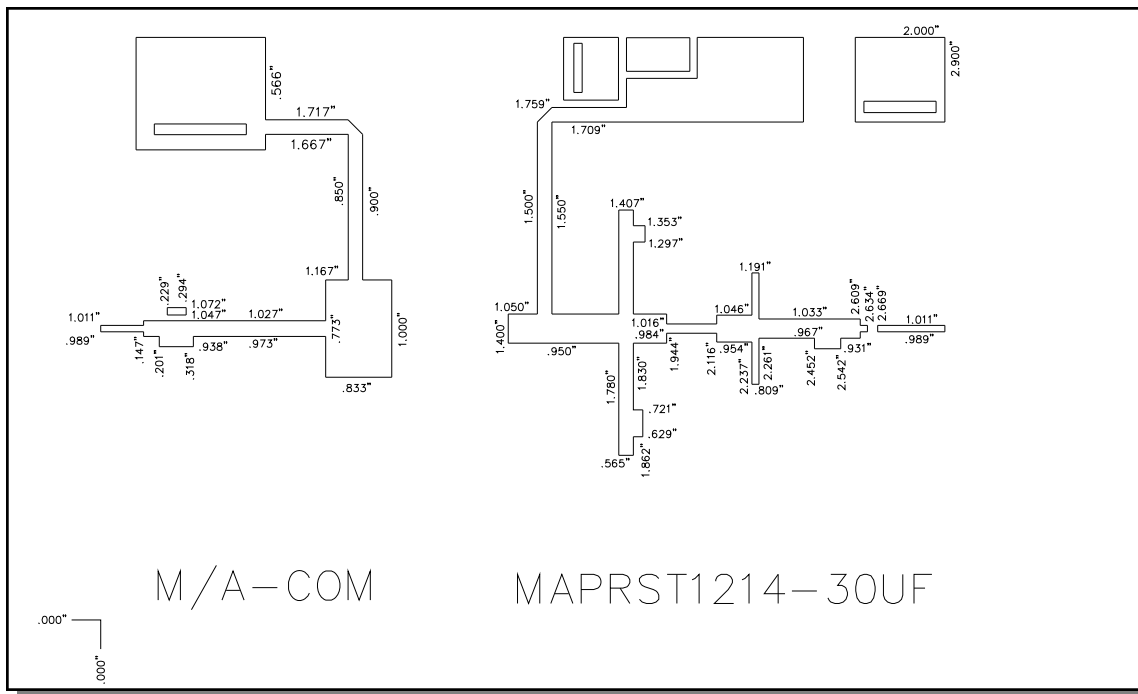
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	6.7 - j6.9	14.3 + j2.4
1.3	6.5 - j6.5	11.2 - j0.8
1.4	6.3 - j4.5	7.2 - j0.1



Radar Pulsed Power Transistor
30W, 1.2-1.4 GHz, 6ms Pulse, 25% Duty

M/A-COM Products
Released, 30 May 07

Test Fixture Circuit Dimensions



Test Fixture Assembly

